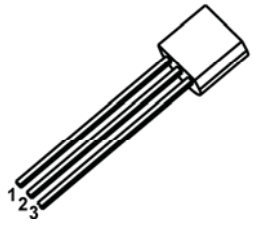
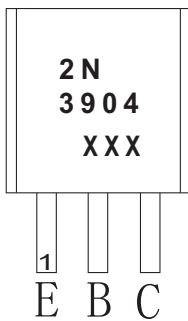


**TO-92 Plastic-Encapsulate Transistors****2N3904** TRANSISTOR (NPN)**FEATURE**

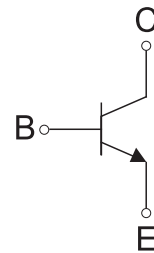
- NPN silicon epitaxial planar transistor for switching and Amplifier applications
- As complementary type, the PNP transistor 2N3906 is Recommended
- This transistor is also available in the SOT-23 case with the type designation MMBT3904

TO-92

1. EMITTER
2. BASE
3. COLLECTOR
- 

MARKING

2N3904=Device code
XXX=Code
GXX=Green molding compound device
CXX=Normal molding compound device

Equivalent Circuit**ORDERING INFORMATION**

Part Number	Package	Packing Method	Pack Quantity
2N3904	TO-92	Bulk	1000pcs/Bag
2N3904-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current -Continuous	0.2	A
P _C	Collector Power Dissipation	0.625	W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55-150	°C

ELECTRICAL CHARACTERISTICS

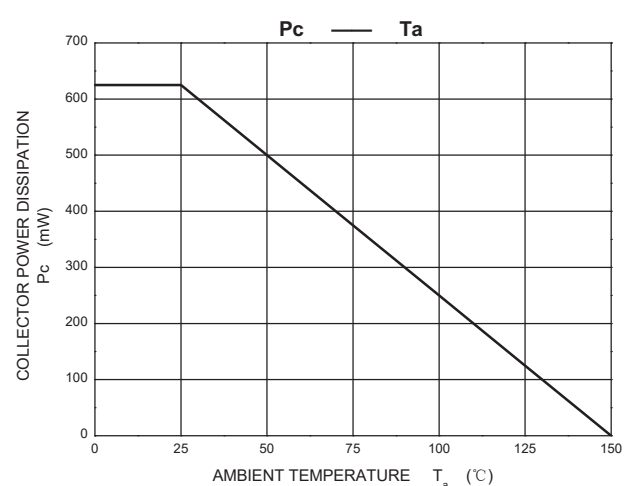
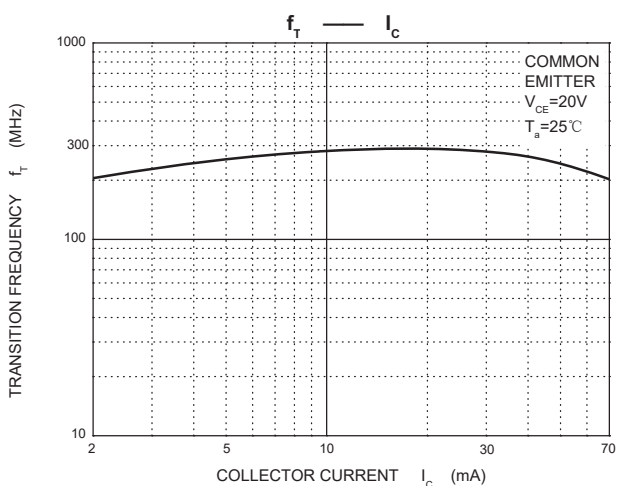
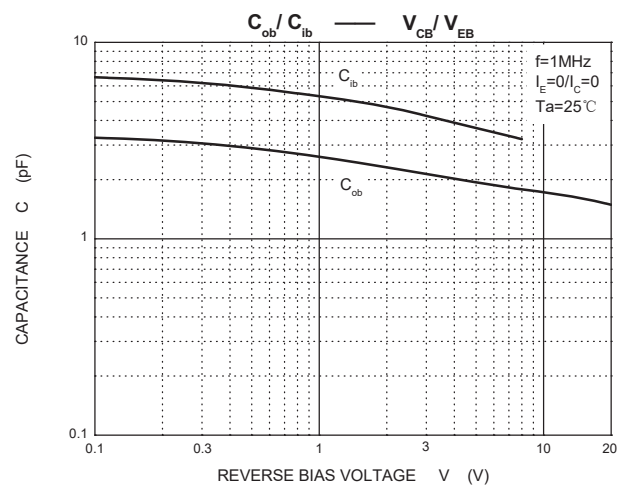
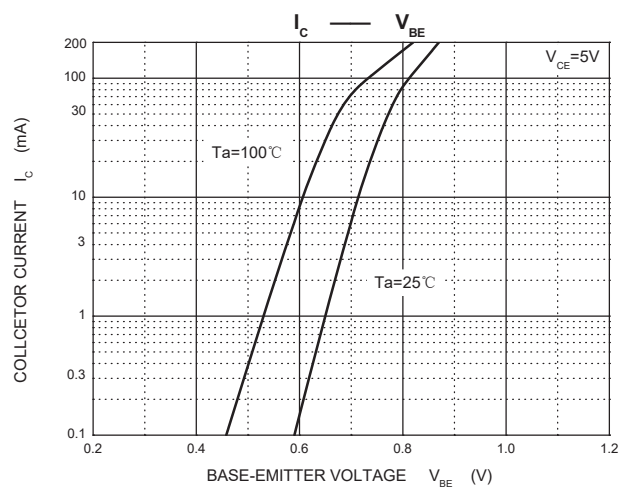
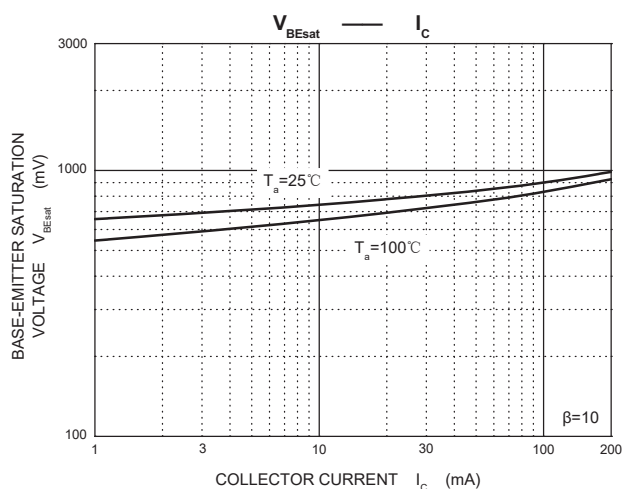
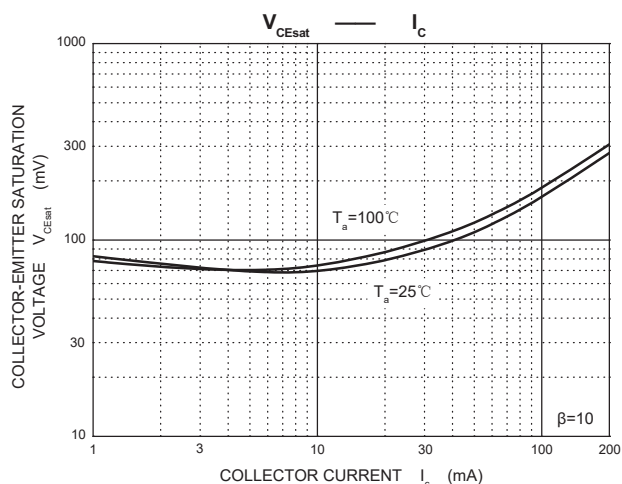
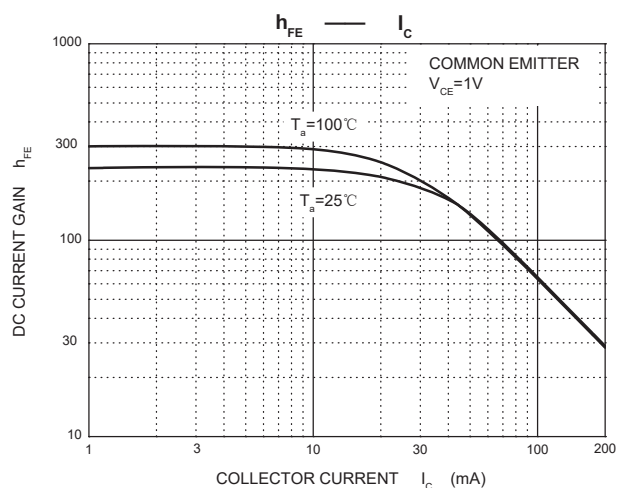
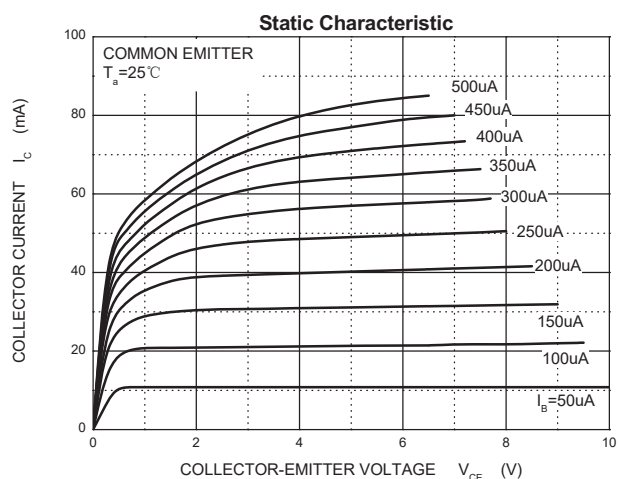
$T_a=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\text{mA}$, $I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}$, $I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\text{mA}$, $I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}$, $I_E=0$			0.1	μA
Collector cut-off current	I_{CEX}	$V_{CE}=30\text{V}$, $V_{EB(off)}=3\text{V}$			0.05	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}$, $I_C=0$			0.1	μA
DC current gain	h_{FE1}	$V_{CE}=1\text{V}$, $I_C=10\text{mA}$	100		400	
	h_{FE2}	$V_{CE}=1\text{V}$, $I_C=50\text{mA}$	60			
	h_{FE3}	$V_{CE}=1\text{V}$, $I_C=100\text{mA}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50\text{mA}$, $I_B=5\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=50\text{mA}$, $I_B=5\text{mA}$			0.95	V
Transition frequency	f_T	$V_{CE}=20\text{V}$, $I_C=10\text{mA}$, $f=100\text{MHz}$	300			MHz
Delay Time	t_d	$V_{CC}=3\text{V}$, $V_{BE}=0.5\text{V}$, $I_C=10\text{mA}$, $I_{B1}=1\text{mA}$			35	ns
Rise Time	t_r				35	ns
Storage Time	t_s	$V_{CC}=3\text{V}$, $I_C=10\text{mA}$ $I_{B1}=I_{B2}=1\text{mA}$			200	ns
Fall Time	t_f				50	ns

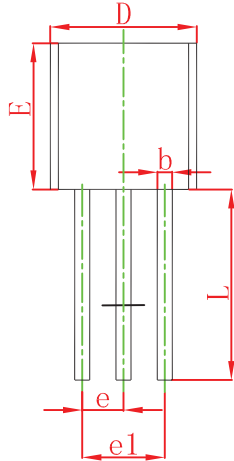
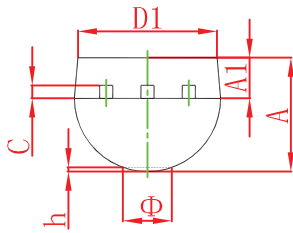
CLASSIFICATION OF h_{FE1}

Rank	O	Y	G
Range	100-200	200-300	300-400

Typical Characteristics

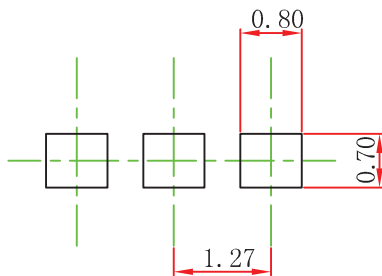


TO-92 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.300	4.700	0.169	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270 TYP		0.050 TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
K		1.600		0.063
h	0.000	0.380	0.000	0.015

TO-92 Suggested Pad Layout

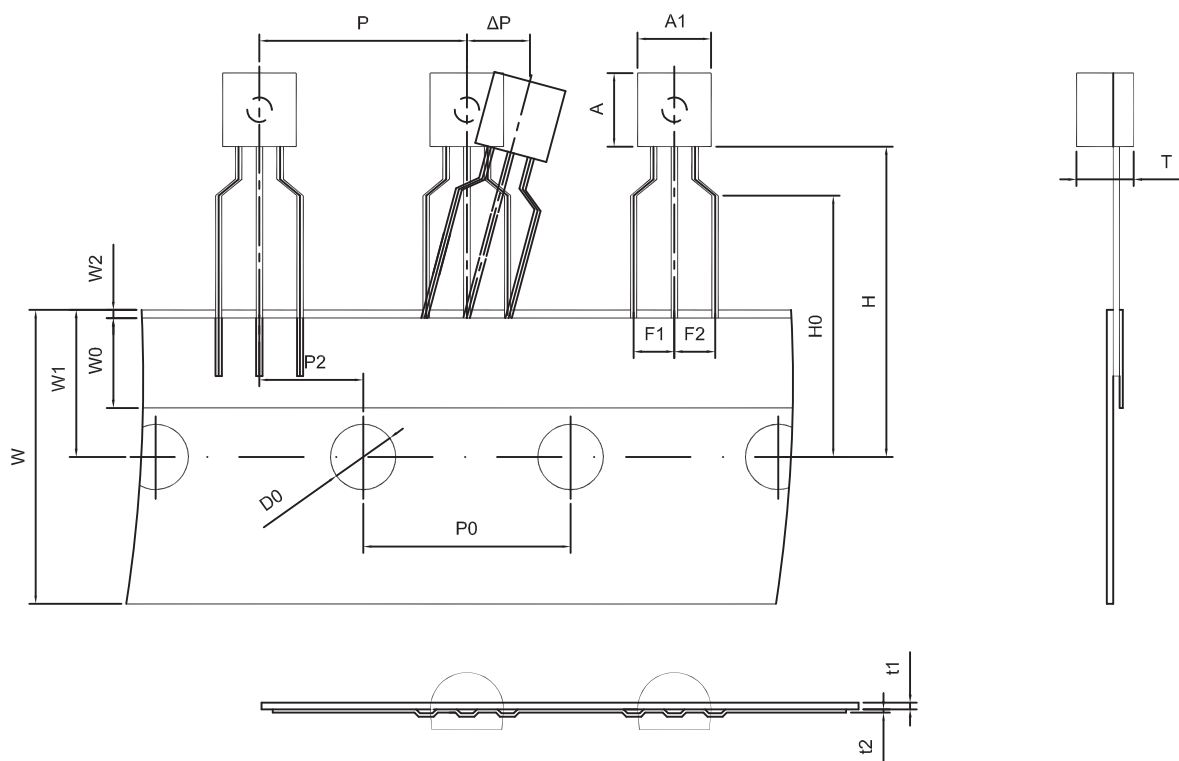


Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.

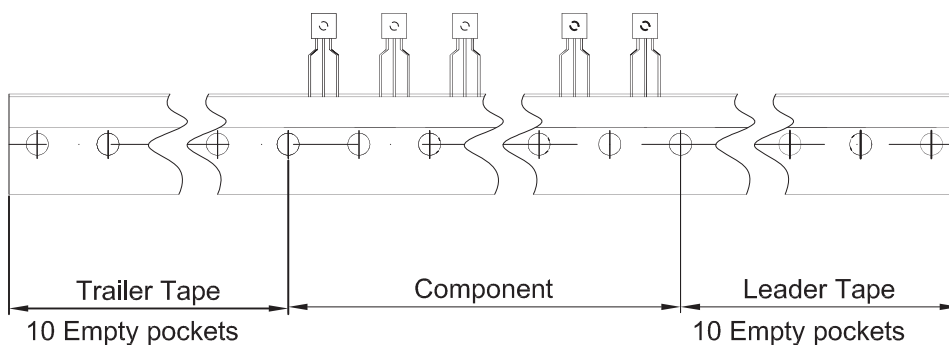
NOTICE

JSCJ reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. JSCJ does not assume any liability arising out of the application or use of any product described herein.



Dimiensions are in millimeter

A1	A	T	P	P0	P2	F1	F2	W
4.5	4.5	3.5	12.7	12.7	6.35	2.5	2.5	18.0
W0	W1	W2	H	H0	D0	t1	t2	ΔP
6.0	9.0	1.0 MAX.	19.0	16.0	4.0	0.4	0.2	0



Package	Box	Box Size(mm)	Carton	Carton Size(mm)
TO-92	2000 pcs	333×162×43	20,000 pcs	350×340×250